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(54) **OLED DISPLAY SUBSTRATE, MANUFACTURING METHOD THEREFOR, AND DISPLAY DEVICE**

(57) An OLED display substrate, a manufacturing method thereof and a display device are provided. The OLED display substrate includes a TFT array layer, a first electrode, a pixel definition layer, an OEL layer and a second electrode arranged on a base substrate. The pixel definition layer is configured to define a plurality of

subpixel regions. A reflection structure surrounds each subpixel region and is capable of reflecting light beams from the OEL layer and beyond an escaping cone in such a manner as to enable at least parts of the light beams to enter the escaping cone.

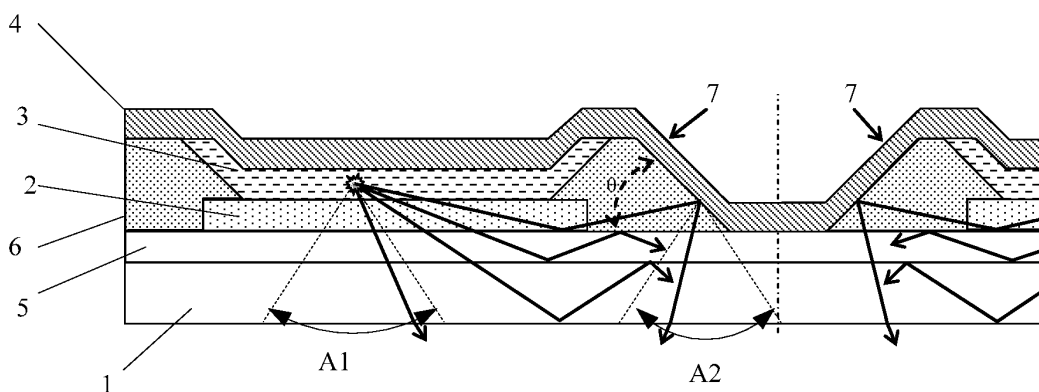


Fig.4

Description

CROSS-REFERENCE TO RELATED APPLICATION

[0001] The present application claims a priority of the Chinese patent application No.201710524515.5 filed on June 30, 2017, which is hereby incorporated by reference in its entirety.

TECHNICAL FIELD

[0002] The present disclosure relates to the field of display technology, in particular to an organic light-emitting diode (OLED) display substrate, a manufacturing method thereof and a display device.

BACKGROUND

[0003] Layers of an OLED device include film layers such as an organic electroluminescence (OEL) layer, a transparent electrode and a substrate, and each of the film layers has a refractive index greater than air. Due to the existence of total reflection, merely parts of light beams from the OEL layer each having an incident angle at each interface in a given light-emitting direction that is smaller than a total reflection angle may exit from the OLED device directly. The light beams generated by a certain light-emitting point (or a secondary light source point) and passing through the interfaces of the film layers form a cone, i.e., an escaping cone. For the OLED device in a bottom-emission (BE) mode, the light beams within the escaping cone may exit from the OLED device directly. The light beams beyond the escaping cone may be totally reflected at different interfaces and then transmitted in the corresponding film layers in a wave guide mode. Usually, a proportion of the number of light beams transmitted in the wave guide mode to the total number of light beams is greater than the number of light beams capable of directly exiting from the OLED device to the total number of light beams. Hence, a luminous efficiency of the OLED device may be significantly adversely affected.

SUMMARY

[0004] An object of the present disclosure is to provide an OLED display substrate, a manufacturing method thereof, and a display device, so as to improve the luminous efficiency of the OLED display device.

[0005] In one aspect, the present disclosure provides in some embodiments an OLED display substrate, including a thin film transistor (TFT) array layer, a first electrode, a pixel definition layer, an OEL layer and a second electrode that are arranged on a base substrate. The pixel definition layer is configured to define a plurality of subpixel regions. A reflection structure is arranged to surround each of the subpixel regions, and is capable of reflecting light beams that are transmitted from the OEL

layer and beyond an escaping cone, to enable at least parts of the reflected light beams to enter the escaping cone.

[0006] In a possible embodiment of the present disclosure, a groove surrounds each subpixel region, and the reflection structure is a reflection layer formed at a side wall of the groove.

[0007] In a possible embodiment of the present disclosure, the groove is formed in the pixel definition layer, and a depth of the groove is not greater than a thickness of the pixel definition layer.

[0008] In a possible embodiment of the present disclosure, the TFT array layer and the pixel definition layer surround each of the subpixel regions, the pixel definition layer is arranged on the TFT array layer, the groove is formed on a laminated structure consisting of the TFT array layer and the pixel definition layer surrounding each of the subpixel regions, and a depth of the groove is greater than a thickness of the pixel definition layer and not greater than a sum of the thickness of the pixel definition layer and a thickness of the TFT array layer.

[0009] In a possible embodiment of the present disclosure, the TFT array layer and the pixel definition layer surround each of the subpixel regions, the pixel definition layer is arranged on the TFT array layer, the groove is formed on a laminated structure consisting of the base substrate, the TFT array layer and the pixel definition layer surrounding each of the subpixel regions, and a depth of the groove is greater than a sum of a thickness of the TFT array layer and a thickness of the pixel definition layer, and smaller than a sum of the thickness of the pixel definition layer, the thickness of the TFT array layer and a thickness of the base substrate.

[0010] In a possible embodiment of the present disclosure, the first electrode is a transparent electrode, the second electrode is a reflective metal electrode, and the reflection layer is made of a same material as the second electrode.

[0011] In a possible embodiment of the present disclosure, the TFT array layer is provided with an opening surrounding each of subpixel regions, and a portion of the pixel definition layer is arranged in the opening.

[0012] In a possible embodiment of the present disclosure, the reflection layer comprises a first portion and a second portion, the first portion is angled relative to the TFT array layer at a first angle, the second portion is angled relative to the pixel definition layer at a second angle, and the first angle is different from the second angle.

[0013] In a possible embodiment of the present disclosure, the reflection layer is of a V-shaped or trapezoidal cross section, and the V-shaped or trapezoidal cross section is perpendicular to an extension direction of the reflection layer.

[0014] In another aspect, the present disclosure provides in some embodiments a display device including the above-mentioned display substrate.

[0015] In yet another aspect, the present disclosure

provides in some embodiments a method for manufacturing an OLED display substrate, including: forming a TFT array layer, a first electrode, a pixel definition layer, an OEL layer and a second electrode sequentially on a base substrate, wherein the pixel definition layer is configured to define a plurality of subpixel regions; and forming a reflection structure surrounding each of the subpixel regions, wherein the reflection structure is capable of reflecting light beams that are transmitted from the OEL layer and beyond an escaping cone, to enable at least parts of the reflected light beams to enter the escaping cone.

[0016] In a possible embodiment of the present disclosure, the forming the TFT array layer includes: forming the TFT array layer that has an opening and surrounds each of the subpixel regions

[0017] In a possible embodiment of the present disclosure, the forming the reflection structure includes: forming a groove surrounding each of the subpixel regions, and forming a reflection layer on a side wall of the groove.

[0018] In a possible embodiment of the present disclosure, the forming the reflection layer includes: forming the second electrode and the reflection layer through a single process.

[0019] In a possible embodiment of the present disclosure, the forming the reflection layer includes: forming a first portion of the reflection layer and a second portion of the reflection layer, wherein the first portion is angled relative to the TFT array layer at a first angle, the second portion is angled relative to the pixel definition layer at a second angle, and the first angle is different from the second angle.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020]

Fig.1 is a schematic view showing a light loss occurring for a bottom-emission OLED display element; Fig.2 is a schematic view showing the propagation of light beams inside the bottom-emission OLED display element;

Fig.3 is a schematic view showing the propagation and the loss of the light beams inside the bottom-emission OLED display element;

Fig.4 is a schematic view showing an OLED display substrate and the propagation of light beams of the OLED display substrate according to some embodiments of the present disclosure;

Fig.5 is a schematic view showing another OLED display substrate and the propagation of the light beams of the OLED display substrate according to some embodiments of the present disclosure;

Figs.6 and 7 are schematic views showing the manufacture of the OLED display substrate according to some embodiments of the present disclosure;

Fig.8 is yet another schematic view showing the OLED display substrate and the propagation of the

light beams of the OLED display substrate according to some embodiments of the present disclosure;

Figs.9-16 are schematic views showing the manufacture of the OLED display substrate according to some embodiments of the present disclosure;

Fig.17 is a schematic view showing still yet another OLED display substrate and the propagation of the light beams of the OLED display substrate according to some embodiments of the present disclosure;

Fig.18 is a schematic view showing the manufacture of the OLED display substrate according to some embodiments of the present disclosure;

Fig.19 is a schematic view showing still yet another OLED display substrate and the propagation of the light beams of the OLED display substrate according to some embodiments of the present disclosure; and Figs.20-21 are schematic views showing still yet other OLED display substrates and the propagation of the light beams of the OLED display substrates according to some embodiments of the present disclosure.

Reference Sign List

[0021]

1	base substrate
2	transparent electrode
3	OEL layer
4	reflective metal electrode
5	TFT array layer
6	pixel definition layer
7	reflection layer
A, A1, A2, A3	escaping cone

DETAILED DESCRIPTION OF THE EMBODIMENTS

[0022] In order to make the objects, the technical solutions and the advantages of the present disclosure more apparent, the present disclosure will be described hereinafter in conjunction with the drawings and embodiments.

[0023] A bottom-emission OLED display element has a relatively complex layer structure. At first, a pixel definition layer (PDL) is arranged surrounding each pixel so as to define a pixel light-emitting region, and no current flows through a region corresponding to the PDL, so the PDL does not emit light. Usually, the PDL is made of a material having a refractive index substantially similar to a light-emitting material of an OLED, so a light beam generated by an OEL layer may pass through an organic light-emitting layer and a transparent electrode layer into the PDL. Next, an OLED pixel structure includes a TFT array layer, and the light beam generated by the OEL layer may enter the TFT array layer. During the transmission of the light beams in the PDL and the TFT array layer, a light loss may occur, i.e., parts of the light beams may not be valid for the display. As shown in Figs. 1 and

2, the light beams generated by the OEL layer 3 may also be reflected at an interface between a base substrate 1 and air, and at an interface between a transparent electrode 2 and the base substrate 1, so an amount of the valid light beams may be further reduced.

[0024] As shown in Figs.2 and 3, for the bottom-emission OLED display element, merely the light beams generated by the OEL layer 3 each having an incident angle in a given light-exiting direction at each interface smaller than a total reflection angle (i.e., the light beams within an escaping cone A) may directly exit from a given light-exiting surface of the OLED display element. Due to the total reflection, the light beams beyond the escaping cone A may be transmitted in the layers in a wave guide mode and finally lost in the OEL layer/transparent electrode, the TFT array layer, and the base substrate. Due to the transmission of the light beams in the wave guide mode, a luminous efficiency of the OLED display element may be reduced.

[0025] An object of the present disclosure is to provide an OLED display substrate, a manufacturing method thereof and a display device, so as to improve the luminous efficiency of the OLED display device.

[0026] According to the embodiments of the present disclosure, a reflection structure is arranged in such layers as a PDL surrounding an OEL layer for each pixel and a TFT array layer, so as to reflect light beams transmitted therein in a wave guide mode. Through selecting a gradient angle of a reflection surface, it is able to reflect the light beams in a given direction, thereby to enable parts of the light beams to exit the wave guide mode and enter an escaping cone and become valid light beams for the display. As a result, it is able to obviously improve the luminous efficiency of the bottom-emission OLED display element.

[0027] The present disclosure provides in some embodiments an OLED display substrate, which includes a TFT array layer, a first electrode, a pixel definition layer, an OEL layer and a second electrode arranged on a base substrate. The pixel definition layer is configured to define a plurality of subpixel regions. A reflection structure surrounds each subpixel region and is capable of reflecting light beams from the OEL layer and beyond an escaping cone in such a manner as to enable at least parts of the light beams to enter the escaping cone.

[0028] According to the OLED display substrate in the embodiments of the present disclosure, the reflection structure surrounds each subpixel region and it is capable of reflecting the light beams from the OEL layer and beyond the escaping cone in such a manner as to enable at least parts of the light beams to enter the escaping cone, i.e., to enable the light beams transmitted in a wave guide mode to exit the wave guide mode and become valid light beams for the display. As a result, it is able to obviously improve the luminous efficiency of a bottom-emission OLED display device.

[0029] To be specific, a groove surrounds each subpixel region, and the reflection structure is a reflection

layer formed at a side wall of the groove.

[0030] In a possible embodiment of the present disclosure, the groove is formed in the pixel definition layer, and has a depth not greater than a thickness of the pixel definition layer.

[0031] In another possible embodiment of the present disclosure, the TFT array layer and the pixel definition layer on the TFT array layer surround each subpixel region, the groove is formed on a laminated structure consisting of the TFT array layer and the pixel definition layer surrounding each subpixel region, and the groove has a depth greater than a thickness of the pixel definition layer and not greater than a sum of the thickness of the pixel definition layer and a thickness of the TFT array layer.

[0032] In yet another possible embodiment of the present disclosure, the TFT array layer and the pixel definition layer on the TFT array layer surround each subpixel region, the groove is formed on a laminated structure consisting of the base substrate, the TFT array layer and the pixel definition layer surrounding each subpixel region, and the groove has a depth greater than a sum of a thickness of the TFT array layer and a thickness of the pixel definition layer and smaller than a sum of the thickness of the pixel definition layer, the thickness of the TFT array layer and a thickness of the base substrate.

[0033] In a possible embodiment of the present disclosure, the first electrode is a transparent electrode, the second electrode is a reflective metal electrode, and the reflection layer is made of a same material as the second electrode. In this way, the reflection layer and the second electrode may be formed through a single photoetching process, so as to reduce the number of photoetching processes during the manufacture of the display substrate.

[0034] In a possible embodiment of the present disclosure, the TFT array layer is provided with an opening surrounding each subpixel region, and a portion of the pixel definition layer is arranged in the opening.

[0035] In a possible embodiment of the present disclosure, the reflection layer includes a first portion angled relative to the TFT array layer at a first angle and a second portion angled relative to the pixel definition layer at a second angle different from the first angle.

[0036] In a possible embodiment of the present disclosure, the reflection layer is of a V-shaped or trapezoidal cross section perpendicular to its extension direction.

[0037] The present disclosure further provides in some embodiments a display device including the above-mentioned display substrate. The display device may be any product or member having a display function, e.g., television, display, digital photo frame, mobile phone or flat-panel computer. The display device may further include a flexible circuit board, a printed circuit board and a back plate.

[0038] The present disclosure further provides in some embodiments a method for manufacturing an OLED display substrate, including: forming a TFT array layer, a first electrode, a pixel definition layer, an OEL layer and

a second electrode sequentially on a base substrate, the pixel definition layer defining a plurality of subpixel regions; and forming a reflection structure surrounding each subpixel region and capable of reflecting light beams from the OEL layer and beyond an escaping cone in such a manner as to enable at least parts of the light beams to enter the escaping cone.

[0039] According to the method in the embodiments of the present disclosure, the reflection structure surrounds each subpixel region, and is capable of reflecting the light beams from the OEL layer and beyond the escaping cone in such a manner as to enable at least parts of the light beams to exit the wave guide mode and enter the become valid light beams for the display. As a result, it is able to significantly improve the luminous efficiency of a bottom-emission OLED display device.

[0040] In a possible embodiment of the present disclosure, the forming the TFT array layer includes: forming the TFT array layer having an opening surrounding each subpixel region.

[0041] In a possible embodiment of the present disclosure, the forming the reflection structure includes: forming a groove surrounding each subpixel region and forming a reflection layer on a side wall of the groove.

[0042] In a possible embodiment of the present disclosure, the forming the reflection layer includes: forming the second electrode and the reflection layer through a single process, so as to reduce the number of photoetching processes during the manufacture of the display substrate.

[0043] In a possible embodiment of the present disclosure, the forming the reflection layer includes: forming a first portion of the reflection layer angled relative to the TFT array layer at a first angle and a second portion of the reflection layer angled relative to the pixel definition layer at a second angle different from the first angle.

[0044] The present disclosure will be described hereinafter in conjunction with the embodiments and drawings in more details.

[0045] In a possible embodiment of the present disclosure, as shown in Fig. 4, the groove may be formed in the pixel definition layer 6 surrounding each subpixel region, and the groove may have a depth equal to the thickness of the pixel definition layer 6. The reflection layer 7 may be formed on the side wall of the groove. A gradient angle θ of the side wall of the groove may be selected in such a manner as to reflect the light beams transmitted in the pixel definition layer in the wave guide mode as many as possible toward an escaping cone A2 and become the valid light beams for the display. Here, the depth of the groove may also be greater than or smaller than the thickness of the pixel definition layer 6, which will be described in more details hereinafter.

[0046] When no reflection structure is provided, merely a part of the light beams generated by the OEL layer 3 within the escaping cone A1 are valid light beams for the display. After the formation of the reflection structure, a part of the light beams generated by the OEL layer 3 may

pass through the transparent electrode 2 (i.e., an anode) into the pixel definition layer 6, and then may be reflected by the reflection layer 7 and enter the escaping cone A2 to become the valid light beams for the display. As a result, it is able to improve the luminous efficiency of the OLED display element.

[0047] During the manufacture of the display substrate, the pixel definition layer 6 is formed on the base substrate 1. When pixel opening regions are formed by the pixel definition layer 6 through a photoetching process, the groove may be formed by the pixel definition layer 6 surrounding each pixel opening region. Then, the OEL layer may be formed through a conventional process, and the reflection layer 7 may be formed on the side wall of the groove while forming the reflective electrode (i.e., a cathode).

[0048] In a possible embodiment of the present disclosure, as shown in Fig. 5, the pixel definition layer 6 may be directly formed on the base substrate 1 between two adjacent subpixel regions, and no TFT array layer 5 may be arranged surrounding each subpixel region. The groove may be formed in the pixel definition layer 6 surrounding each subpixel region, and the groove may have a depth equal to the thickness of the pixel definition layer 6. The reflection layer 7 may be formed on the side wall of the groove, and the gradient angle θ of the side wall of the groove may be selected in such a manner as to reflect the light beams transmitted in the pixel definition layer in the wave guide mode as many as possible toward an escaping cone A2 to become the valid light beams for the display.

[0049] Here, the light beams are transmitted in the wave guide mode in the OEL layer/transparent electrode and the base substrate, rather than in the TFT array layer. When no reflection structure is formed, merely the light beams generated by the OEL layer 3 within the escaping cone A1 may become the valid light beams for the display. After the formation of the reflection structure, the light beams in the OEL layer/transparent electrode mode may pass through the OEL layer 3 and the transparent electrode 1 (i.e., the anode) into the pixel definition layer 6, and then reflected by the reflection layer 7, and a part of the reflected light beams enters the escaping cone A2 to become the valid light beams for the display. As a result, it is able to improve the luminous efficiency of the OLED display element.

[0050] As shown in Figs. 6 and 7, after the formation of the TFT array layer 5 on the base substrate 1, an additional photoetching process may be provided so as to remove a portion of the TFT array layer 5 surrounding each subpixel region. Alternatively, the portion of the TFT array layer 5 surrounding each subpixel region may also be removed through a last photoetching process or several last photoetching processes (usually for the formation of via-holes) of the display substrate, and then the pixel definition layer 6 and the other layers thereon may be formed through conventional processes.

[0051] In a possible embodiment of the present disclosure,

sure, as shown in Fig.8, the pixel definition layer 6 may be formed on the base substrate 1 surrounding each subpixel region, and the TFT array layer 5 may surround each subpixel region. The groove may be formed in a laminated structure consisting of the pixel definition layer 6 and the TFT array layer 5 surrounding each subpixel region, and the groove may have a depth equal to a sum of the thickness of the pixel definition layer 6 and the thickness of the TFT array layer 5. The reflection layer 7 may be formed on the side wall of the groove. A gradient angle θ_1 of the side wall of the groove corresponding to the pixel definition layer 6 and a gradient angle θ_2 of the side wall of the groove corresponding to the TFT array layer 5 may be selected in such a manner as to reflect the light beams transmitted in the pixel definition layer and the TFT array layer in the wave guide mode as many as possible toward the escaping cone A2 and an escaping cone A3 respectively to become the valid light beams for the display. To be specific, values of θ_1 and θ_2 may be set in accordance with the distribution of the light beams transmitted in the layers in the wave guide mode and optical characteristics of materials of the layers (mainly refractive indices). It should be appreciated that, in a planar wave guide, the light beams are reflected by an upper interface and a lower interface alternately so as to travel in a wave form, so the light beams are not transmitted toward the reflection surface horizontally, i.e., each light beam may reach the reflection surface at a certain elevation or depression angle. Here, the values of θ_1 and θ_2 may be calculated through a mathematical formula in accordance with such parameters as the elevation or depression angles, wavelengths of the light beams, a thickness of the wave guide, and a return loss at a reflection surface between a wave guide medium and an adjacent medium. Usually, each of θ_1 and θ_2 may be smaller than or equal to 45° . For example, in the PDL layer, θ_1 may be in a range from 30° to 35° .

[0052] When no reflection structure is formed, merely the part of the light beams generated by the OEL layer 3 within the escaping cone A1 may be the valid light beams for the display. After the formation of the reflection structure, the light beams in the OEL layer/transparent electrode mode may pass through the OEL layer 3 and the transparent electrode 1 (i.e., the anode) into the pixel definition layer 6, and then reflected by the reflection layer 7, and a part of the reflected light beams enters the escaping cone A2 to come the valid light beams for the display. Identically, the light beams in the wave guide mode may pass through the TFT array layer 5, and be reflected by the reflection layer 7, and then a part of the reflected light beams enters the escaping cone A3 to become the valid light beams for the display. As a result, it is able to improve the luminous efficiency of the OLED display element.

[0053] As shown in Fig.9, during the manufacture of the display substrate, the TFT array layer 5 may be formed at first on the base substrate 1. As shown in Fig.10, after the formation of the TFT array layer 5, an

additional photoetching process may be provided so as to remove a portion of the TFT array layer 5 surrounding the pixel light-emitting region. In addition, the portion of the TFT array layer 5 at the corresponding region may also be removed through a last photoetching process or several last photoetching processes (usually for the formation of via-holes) during manufacturing of the display substrate. As shown in Fig.11, the transparent electrode 2 may be formed. As shown in Fig.12, finally a pattern of the pixel definition layer 6 may be formed through a photoetching process.

[0054] In addition, as shown in Figs.13 and 14, after the formation of the groove in the pixel definition layer 6, an additional etching process with the pixel definition layer 6 and the transparent electrode 2 as a mask plate may be provided so as to remove the portion of the TFT array layer 5 surrounding the pixel light-emitting region. In this way, the groove in the pixel definition layer 6 may be aligned automatically with the groove in the TFT array layer 5, so it is able to control a shape of the entire reflection interface and improve the reflection performance.

[0055] And then after that, as shown in Fig.15, the OEL layer 3 may be formed at the pixel light-emitting region through printing or evaporation. As shown in Fig.16, a reflective metal layer may be formed through evaporation, so as to form the reflective electrode 4 and the reflection layer 7 simultaneously. The reflective metal layer on the side wall of the groove may form the reflection layer 7.

[0056] In a possible embodiment of the present disclosure, as shown in Fig.17, the TFT array layer 5 may be formed on the base substrate surrounding each subpixel region, and the pixel definition layer 6 may be formed on the TFT array layer 5. The groove may be formed in a laminated structure consisting of the base substrate 1, the TFT array layer 5 and the pixel definition layer 6 surrounding each subpixel region, and the groove may have a depth equal to a sum of the thickness of the pixel definition layer 6, the thickness of the TFT array layer 5 and a thickness of a part of the base substrate 1, i.e., the groove may extend into a part of the base substrate 1. The reflection layer 7 may be formed on the side wall of the groove. A gradient angle of a part of the side wall of the groove corresponding to the pixel definition layer 6, a gradient angle of a part of the side wall of the groove corresponding to the TFT array layer 5 and a gradient angle of a part of the side wall of the groove corresponding to the base substrate 1 may be selected in such a manner as to reflect the light beams transmitted in the pixel definition layer, the base substrate, and the TFT array layer in the wave guide mode as many as possible toward the escaping cones A2 and A3, to become the valid light beams for the display. To be specific, the values of these gradient angles may be set in accordance with the distribution of the light beams transmitted in the layers in the wave guide mode and the optical characteristics of the materials of the layers (mainly the refractive indices).

[0057] Considering features of the etching process, it is very difficult to ensure a gradient of a bottom of a side wall of the TFT array layer 5 relative to a surface of the base substrate 1 to be consistent with a main portion of the side wall of the groove, and a transitional arc surface may easily be formed. When the groove extends into the base substrate, it is able to ensure the consistency of the reflection layer 7 on the side wall of the entire groove, thereby to improve a reflection effect. In addition, when the reflection layer 7 extends into a part of the base substrate 1, it is able to reflect a part of the light beams transmitted in the base substrate in the wave guide mode, thereby to increase the amount of the valid light beams for the display.

[0058] As shown in Fig.18, subsequent to the etching process for removing a portion of the TFT array layer 5, an additional etching process of the base substrate with the TFT array layer 5 as a mask plate may be provided, so as to enable the groove to extend into the base substrate 1.

[0059] In a possible embodiment of the present disclosure, as shown in Fig.19, the pixel definition layer 6 may be formed on the base substrate 1 surrounding each subpixel region, and no TFT array layer 5 may be arranged surrounding each subpixel region. The groove may be formed in the pixel definition layer 6 surrounding each subpixel region, and the groove may have a depth equal to a sum of the thickness of the pixel definition layer 6 and the thickness of the TFT array layer 5. The reflection layer 7 may be formed on the side wall of the groove. The gradient angle of the side wall of the groove may be selected in such a manner as to reflect the light beams transmitted in the pixel definition layer and the TFT array layer in the wave guide mode as many as possible toward the escaping cones A2 and A3 to become the valid light beams for the display. To be specific, the values of the gradient angles may be set in accordance with the distribution of the light beams transmitted in the layers in the wave guide mode and the optical characteristics of the materials of the layers (mainly the refractive indices).

[0060] When no reflection structure is formed, merely the light beams generated by the OEL layer 3 within the escaping cone A1 may be the valid light beams for the display. After the formation of the reflection structure, the light beams in the OEL layer/transparent electrode mode may pass through the OEL layer 3 and the transparent electrode 1 (i.e., the anode) into the pixel definition layer 6, and then be reflected by the reflection layer 7, and then a part of the reflected light beams enters the escaping cone A2 to become the valid light beams for the display. Identically, the light beams transmitted in the TFT array layer 5 in the wave guide mode may be reflected by the reflection layer 7, and a part of the reflected light beams enters the escaping cone A3 to become the valid light beams for the display. As a result, it is able to improve the luminous efficiency of the OLED display element.

[0061] After the formation of the TFT array layer 5 on the base substrate 1, an additional photoetching process

may be provided so as to remove a portion of the TFT array layer 5 surrounding the subpixel region. In addition, the portion of the TFT array layer 5 surrounding the subpixel region may also be removed through a last photoetching process or several last photoetching processes of the display substrate (usually for the formation of vias), and then the pixel definition layer 6 and the other layers thereon may be formed through the conventional processes.

[0062] In the embodiments of the present disclosure, the OEL layer of the display substrate may be formed at regions corresponding to pixels (or subpixels) through Fine Metal Mask (FMM) evaporation or printing. Due to the cost of a mainstream FMM evaporation process and the yield thereof in the prior art, it is necessary to prevent the use of an FMM-based pattern alignment evaporation process as possible.

[0063] In addition, as shown in Figs.20 and 21, merely a part of the OEL layer may be formed with local patterns in the pixels (or subpixels) alignment process, and the other part of the OEL layer may be formed as a whole of the display region by evaporation. An electron injection layer, a hole injection layer, an electron transfer layer and a hole transfer layer may be formed through a single evaporation process, but the portions of the OEL layer corresponding to the subpixels in different colors may be formed through an FMM-based pattern alignment evaporation process with the subpixels being aligned. As shown in Fig.21, the current flows through merely the pixel opening region defined by the pixel definition layer 6 (i.e., the region indicated by a black line in the organic light-emitting layer 3), and merely such pixel opening region emits light.

[0064] In the above two cases, the OEL layer may be deposited on the side wall of the groove in the pixel definition layer 6 or in the pixel definition layer 6 and the TFT array layer 5 before the deposition of the reflection layer 7. Strictly speaking, the reflection interface on the side wall is an interface between the OEL layer 3 and the reflection layer 7, rather than an interface between the reflection layer 7 and the pixel definition layer 6 or the TFT array layer 5. The OEL layer 3 is transparent and has a refractive index substantially similar to the pixel definition layer 6, no difference in the optical properties may occur in the embodiments of the present disclosure, which will not be particularly defined herein.

[0065] For the OLED device in an inverted BE mode, i.e., the transparent cathode, the OEL layer (or the OEL layers) and the reflective anode are formed sequentially on the base substrate. Currently, a process for manufacturing the OLED device in the inverted BE mode is not mature, and a major problem lies in that the OEL layer may be damaged when the cathode (usually made of indium tin oxide (ITO)) is formed through sputtering, so this process has not been applied in mass production. When the process becomes mature in future, for the OLED display device in the inverted BE mode, the OEL layer and the reflective anode may be formed through a single

photoetching process.

[0066] Unless otherwise defined, any technical or scientific term used herein shall have the common meaning understood by a person of ordinary skills. Such words as "first" and "second" used in the specification and claims are merely used to differentiate different components rather than to represent any order, number or importance. Similarly, such words as "one" or "one of" are merely used to represent the existence of at least one member, rather than to limit the number thereof. Such words as "connect" or "connected to" may include electrical connection, direct or indirect, rather than to be limited to physical or mechanical connection. Such words as "on", "under", "left" and "right" are merely used to represent relative position relationship, and when an absolute position of the object is changed, the relative position relationship will be changed too.

[0067] It should be appreciated that, in the case that such an element as layer, film, region or substrate is arranged "on" or "under" another element, it may be directly arranged "on" or "under" the other element, or an intermediate element may be arranged therebetween.

[0068] The above embodiments are merely preferred embodiments of the present disclosure. Obviously, a person skilled in the art may make further modifications and improvements without departing from the spirit of the present disclosure, and these modifications and improvements shall also fall within the scope of the present disclosure.

Claims

1. An organic light-emitting diode (OLED) display substrate, comprising:

a thin film transistor (TFT) array layer, a first electrode, a pixel definition layer, an organic electroluminescence (OEL) layer and a second electrode that are arranged on a base substrate, wherein the pixel definition layer is configured to define a plurality of subpixel regions; and a reflection structure is arranged to surround each of the subpixel regions, and is capable of reflecting light beams that are transmitted from the OEL layer and beyond an escaping cone, to enable at least parts of the reflected light beams to enter the escaping cone.

2. The OLED display substrate according to claim 1, wherein
a groove surrounds each of the subpixel regions, and the reflection structure is a reflection layer formed at a side wall of the groove.
3. The OLED display substrate according to claim 2, wherein
the groove is formed in the pixel definition layer, and

a depth of the groove is not greater than a thickness of the pixel definition layer.

4. The OLED display substrate according to claim 2, wherein
the TFT array layer and the pixel definition layer surround each of the subpixel regions, the pixel definition layer is arranged on the TFT array layer, the groove is formed on a laminated structure consisting of the TFT array layer and the pixel definition layer surrounding each of the subpixel regions, and a depth of the groove is greater than a thickness of the pixel definition layer and not greater than a sum of the thickness of the pixel definition layer and a thickness of the TFT array layer.
5. The OLED display substrate according to claim 2, wherein
the TFT array layer and the pixel definition layer surround each of the subpixel regions, the pixel definition layer is arranged on the TFT array layer, the groove is formed on a laminated structure consisting of the base substrate, the TFT array layer and the pixel definition layer surrounding each of the subpixel regions, and a depth of the groove is greater than a sum of a thickness of the TFT array layer and a thickness of the pixel definition layer, and smaller than a sum of the thickness of the pixel definition layer, the thickness of the TFT array layer and a thickness of the base substrate.
6. The OLED display substrate according to any one of claims 2 to 5, wherein
the first electrode is a transparent electrode, the second electrode is a reflective metal electrode, and the reflection layer is made of a same material as the second electrode.
7. The OLED display substrate according to any one of claims 2 to 5, wherein
the TFT array layer is provided with an opening surrounding each of the subpixel regions, and a portion of the pixel definition layer is arranged in the opening.
8. The OLED display substrate according to claim 4 or 5, wherein
the reflection layer comprises a first portion and a second portion, the first portion is angled relative to the TFT array layer at a first angle, the second portion is angled relative to the pixel definition layer at a second angle, and the first angle is different from the second angle.
9. The OLED display substrate according to any one of claims 2 to 5, wherein
the reflection layer is of a V-shaped or trapezoidal cross section, and the V-shaped or trapezoidal cross section is perpendicular to an extension direction of

the reflection layer.

10. A display device, comprising the OLED display substrate according to any one of claims 1 to 9.

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11. A method for manufacturing an OLED display substrate, comprising:

forming a TFT array layer, a first electrode, a pixel definition layer, an OEL layer and a second electrode sequentially on a base substrate, wherein the pixel definition layer is configured to define a plurality of subpixel regions; and forming a reflection structure surrounding each of the subpixel regions, wherein the reflection structure is capable of reflecting light beams that are transmitted from the OEL layer and beyond an escaping cone, to enable at least parts of the reflected light beams to enter the escaping cone.

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12. The method according to claim 11, wherein the forming the TFT array layer comprises:
forming the TFT array layer that has an opening surrounding each of the subpixel regions.

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13. The method according to claim 11 or 12, wherein the forming the reflection structure comprises:
forming a groove surrounding each of the subpixel regions, and forming a reflection layer on a side wall of the groove.

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14. The method according to claim 13, wherein the forming the reflection layer comprises:
forming the second electrode and the reflection layer through a single process.

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15. The method according to claim 13, wherein the forming the reflection layer comprises:
forming a first portion of the reflection layer and a second portion of the reflection layer, wherein the first portion is angled relative to the TFT array layer at a first angle, the second portion is angled relative to the pixel definition layer at a second angle, and the first angle is different from the second angle.

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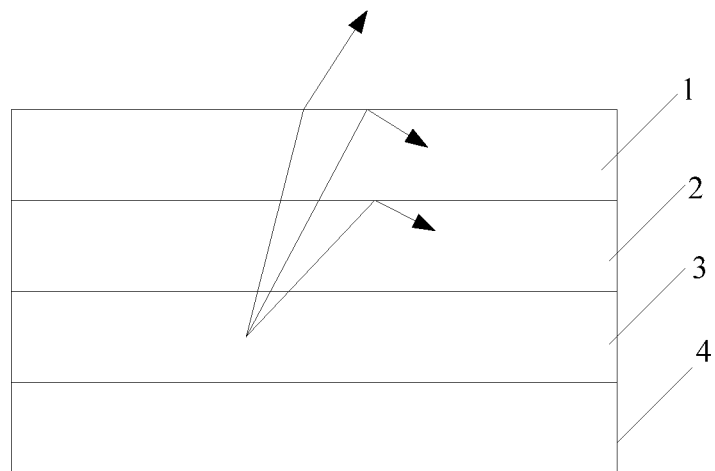


Fig.1

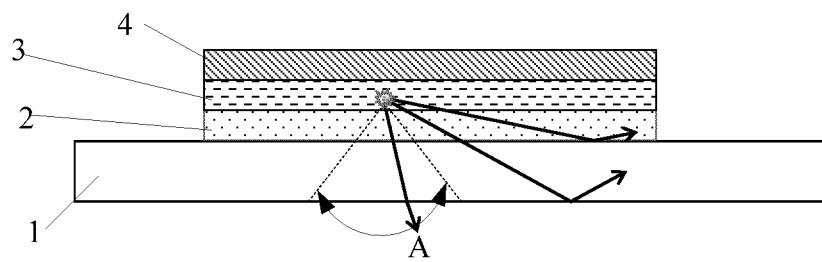


Fig.2

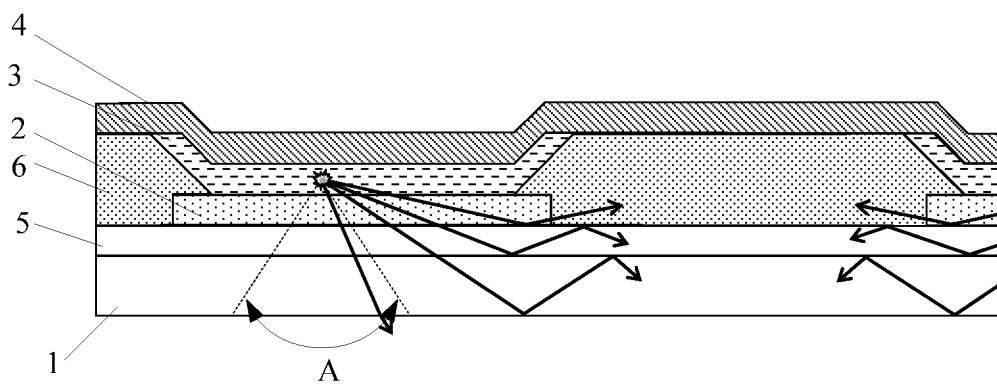


Fig.3

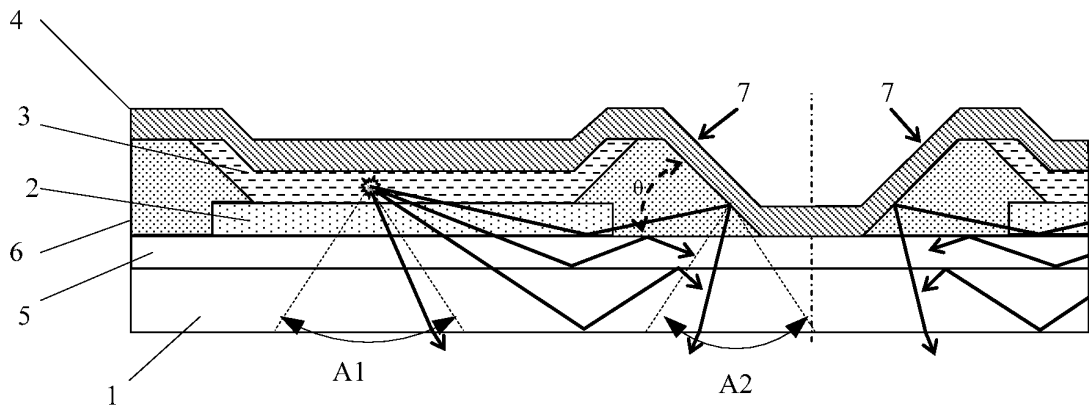


Fig.4

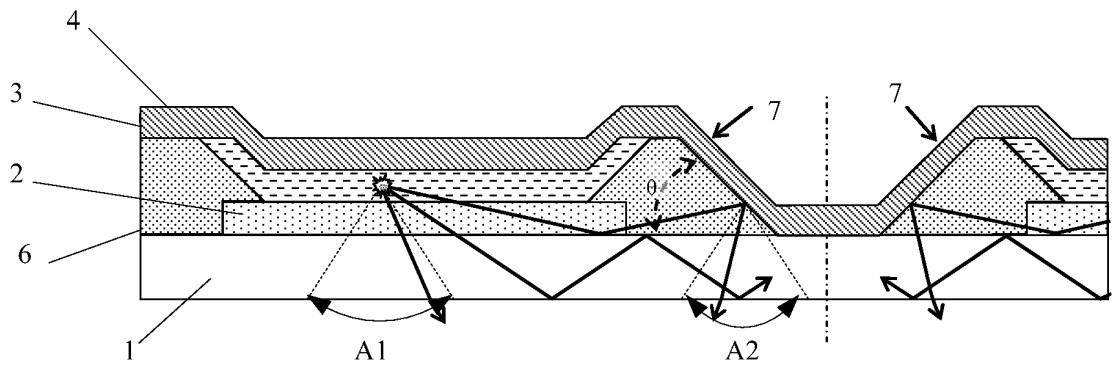


Fig.5

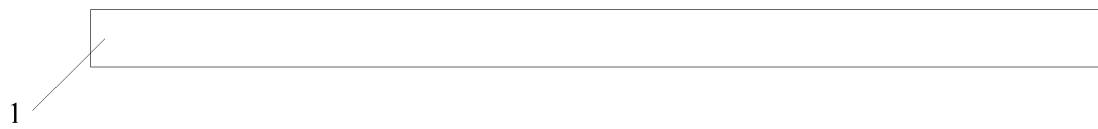


Fig.6

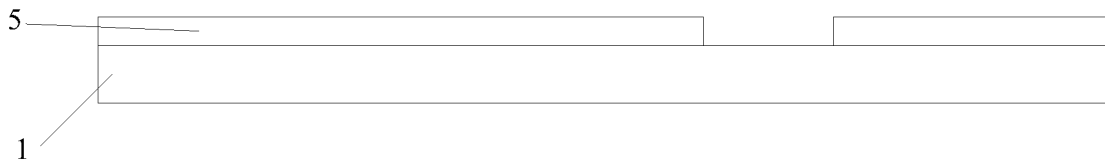


Fig.7

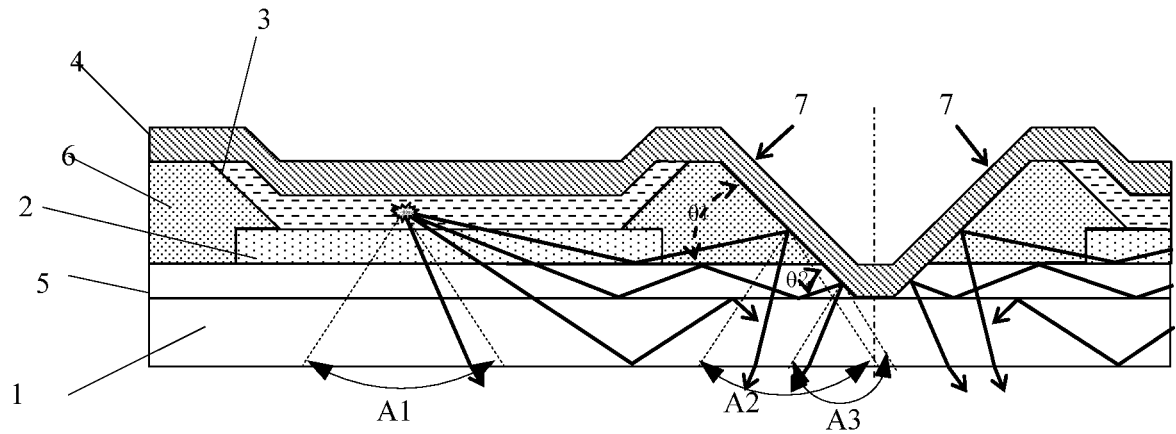


Fig. 8

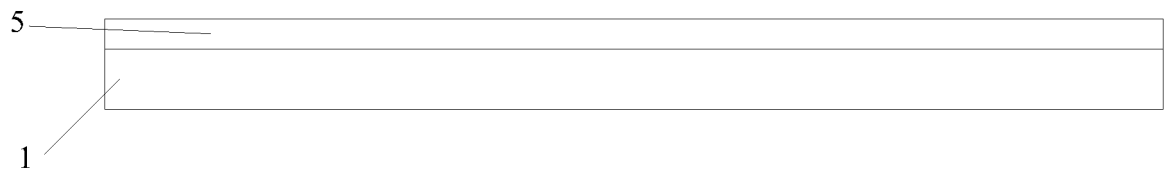


Fig. 9

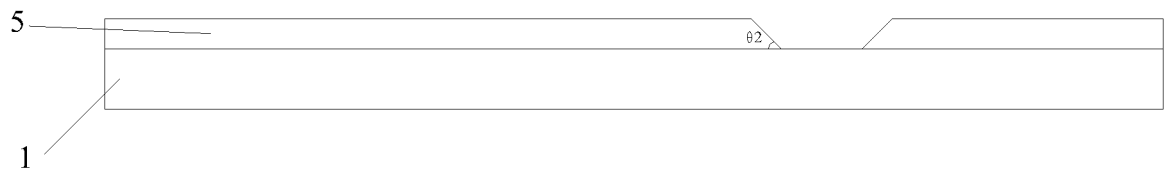


Fig. 10

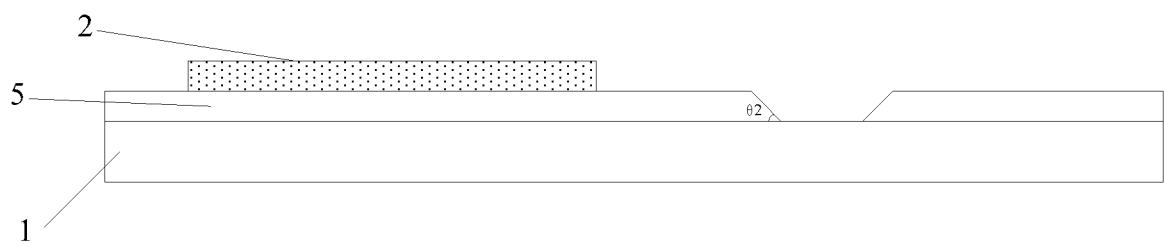


Fig. 11

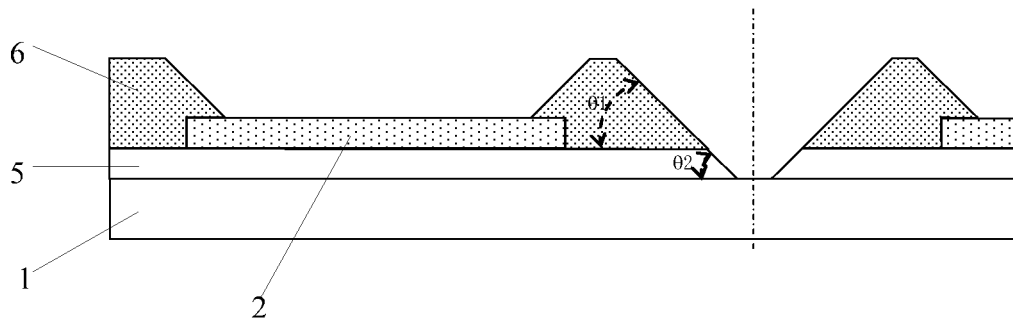


Fig.12

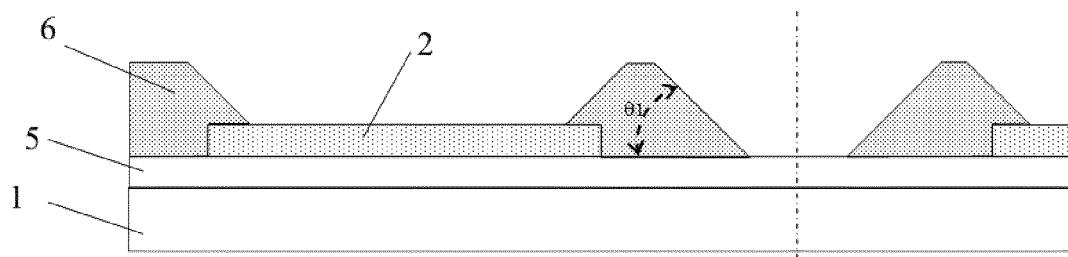


Fig.13

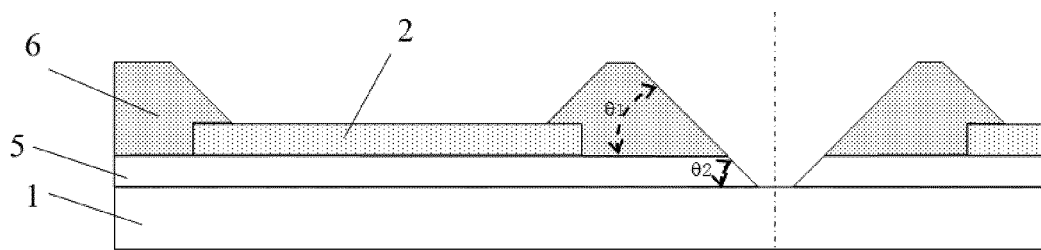


Fig.14

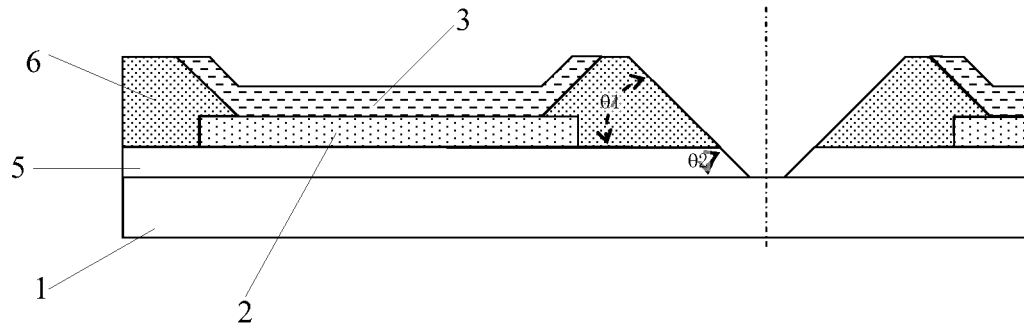


Fig.15

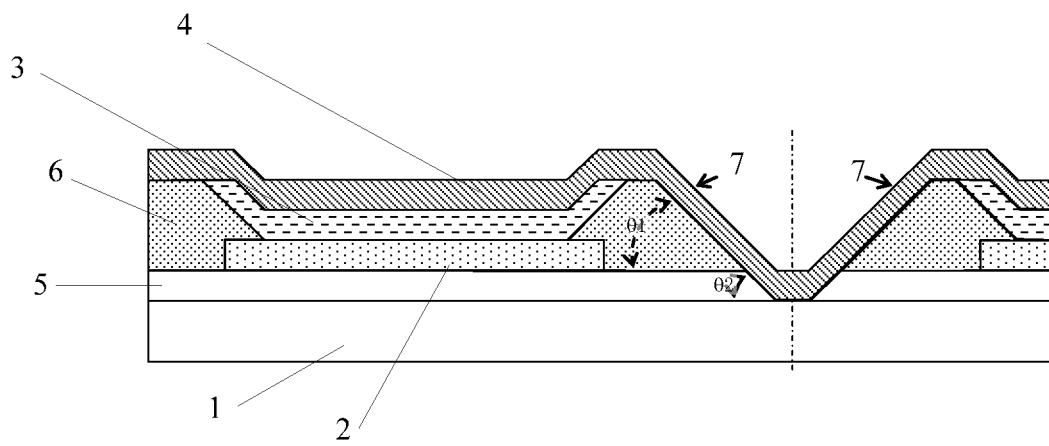


Fig.16

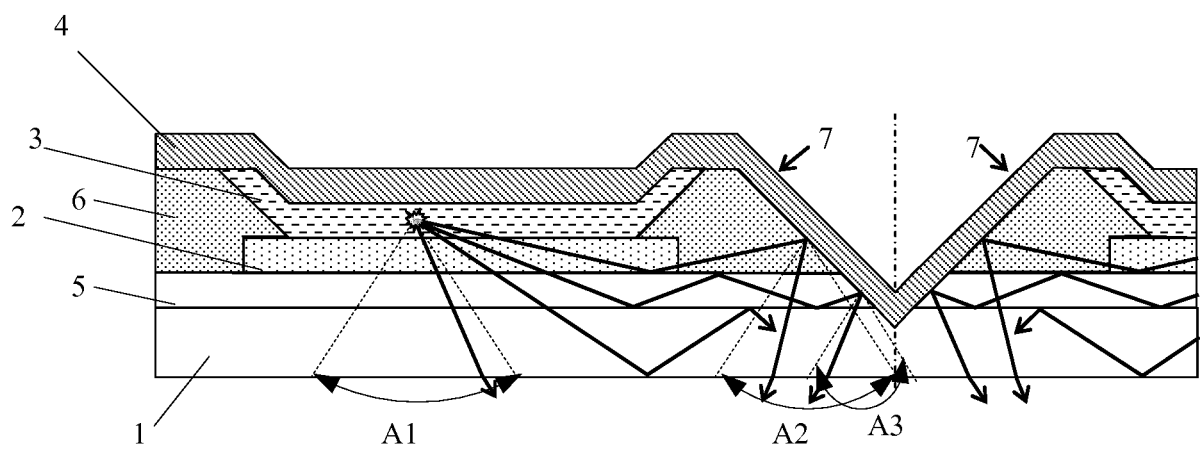


Fig.17

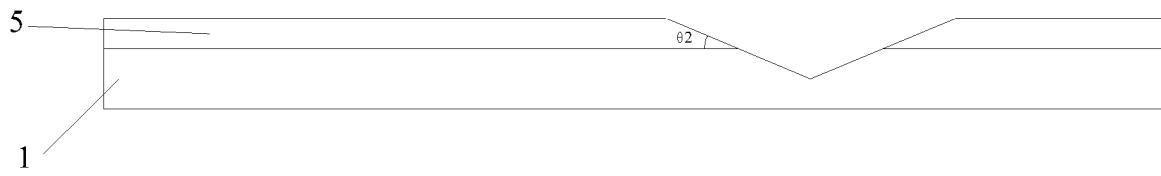


Fig.18

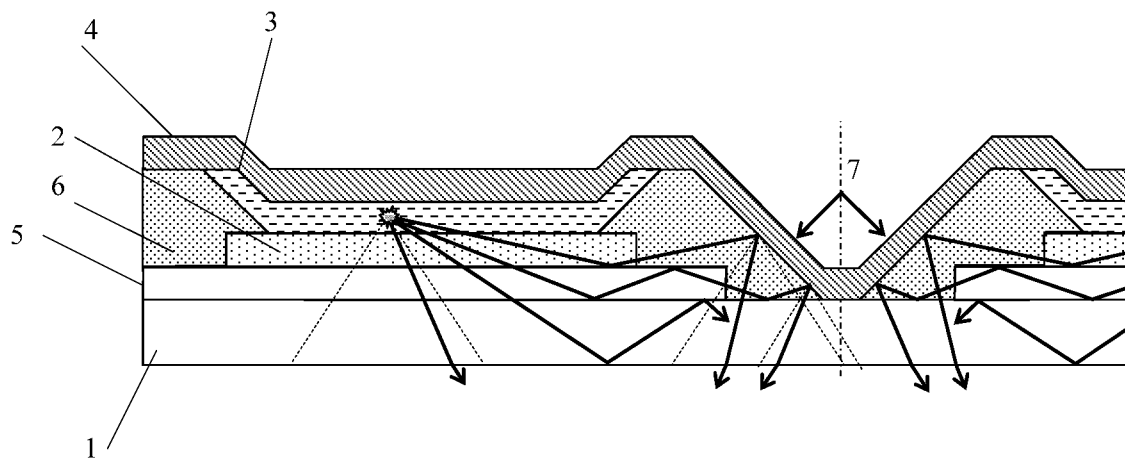


Fig.19

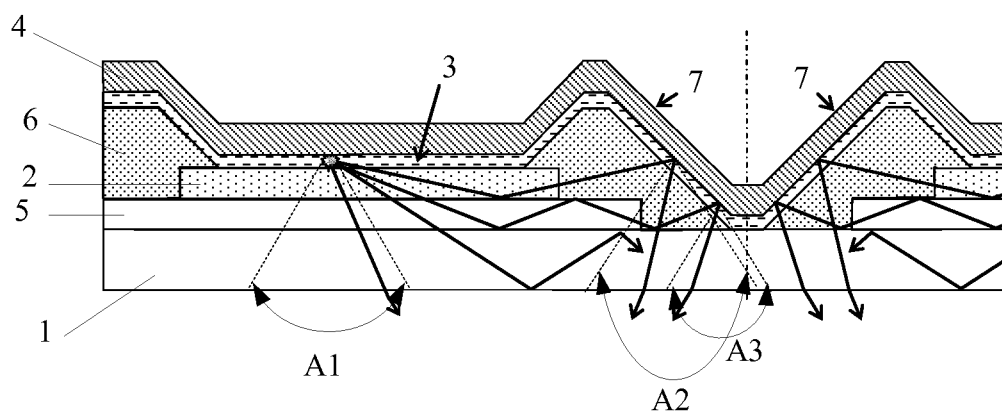


Fig.20

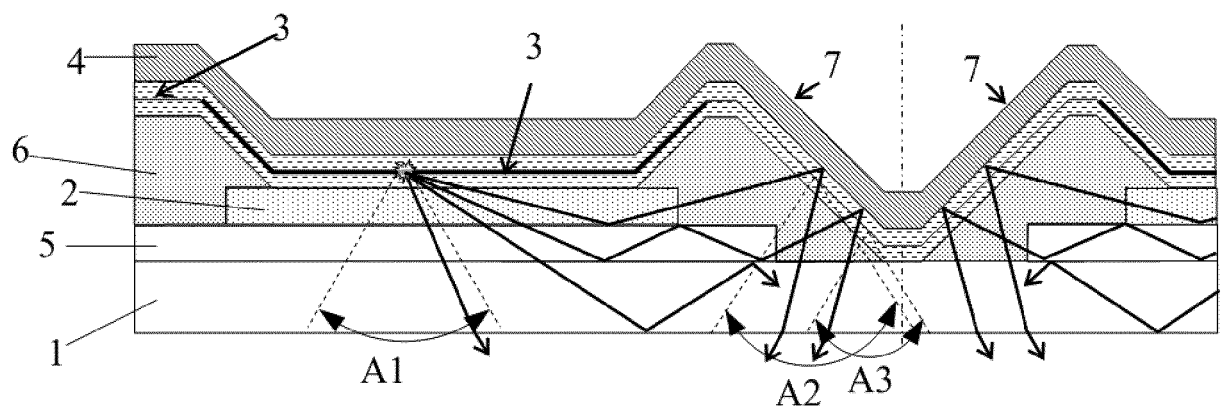


Fig.21

INTERNATIONAL SEARCH REPORT

International application No.

PCT/CN2018/072084

A. CLASSIFICATION OF SUBJECT MATTER

H01L 51/52 (2006.01) i; H01L 27/32 (2006.01) i; H01L 51/56 (2006.01) i

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L 51; H01L 27; H05B 33

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

CNABS, CNTXT, CNKI, SIPOABS, DWPI: 有机, 显示, 电致发光, 场致发光, 像素, 限定, 界定, 分隔, 墙, 堤, 凹槽, 沟槽, 反光, 反射, OLED, organic, display, electroluminescence, pixel, define, wall, bank, partition, groove, recess, reflect

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	CN 1510974 A (SAMSUNG SDI CO., LTD.), 07 July 2004 (07.07.2004), description, page 4, line 3 to page 6, line 22, and figures 2-5	1-15
X	CN 101026180 A (TOPPOLY OPTOELECTRONICS CORP.), 29 August 2007 (29.08.2007), description, page 4, line 1 to page 6, line 6, and figures 2-4	1-15
X	US 2008169461 A1 (SAMSUNG ELECTRONICS CO., LTD.), 17 July 2008 (17.07.2008), description, paragraphs 0078-0132, and figures 3-18	1-15
PX	CN 107170904 A (BOE TECHNOLOGY GROUP CO., LTD.), 15 September 2017 (15.09.2017), claims 1-15, and description, paragraphs 0044-0096	1-15

☐ Further documents are listed in the continuation of Box C.☒ See patent family annex.

* Special categories of cited documents:	"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"A" document defining the general state of the art which is not considered to be of particular relevance	
"E" earlier application or patent but published on or after the international filing date	"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O" document referring to an oral disclosure, use, exhibition or other means	
"P" document published prior to the international filing date but later than the priority date claimed	"&" document member of the same patent family

Date of the actual completion of the international search 08 April 2018	Date of mailing of the international search report 17 April 2018
Name and mailing address of the ISA State Intellectual Property Office of the P. R. China No. 6, Xitucheng Road, Jimenqiao Haidian District, Beijing 100088, China Facsimile No. (86-10) 62019451	Authorized officer XU, Ying Telephone No. (86-10) 62412106

Form PCT/ISA/210 (second sheet) (July 2009)

INTERNATIONAL SEARCH REPORT
Information on patent family members

International application No.
PCT/CN2018/072084

Patent Documents referred in the Report	Publication Date	Patent Family	Publication Date
CN 1510974 A	07 July 2004	US 2004119398 A1	24 June 2004
		JP 2004207218 A	22 July 2004
		CN 100470824 C	18 March 2009
		KR 20040055223 A	26 June 2004
		US 7815479 B2	19 October 2010
		KR 100521272 B1	12 October 2005
		JP 4307186 B2	05 August 2009
		US 2008220683 A1	11 September 2008
CN 101026180 A	29 August 2007	US 7391151 B2	24 June 2008
		CN 100483731 C	29 April 2009
		US 2007194696 A1	23 August 2007
		US 7535163 B2	19 May 2009
US 2008169461 A1	17 July 2008	KR 20080067158 A	18 July 2008
CN 107170904 A	15 September 2017	None	

Form PCT/ISA/210 (patent family annex) (July 2009)

REFERENCES CITED IN THE DESCRIPTION

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Patent documents cited in the description

- CN 201710524515 [0001]

专利名称(译)	OLED显示基板，其制造方法以及显示装置		
公开(公告)号	EP3648190A1	公开(公告)日	2020-05-06
申请号	EP2018823282	申请日	2018-01-10
[标]申请(专利权)人(译)	京东方科技集团股份有限公司		
申请(专利权)人(译)	京东方科技集团股份有限公司.		
当前申请(专利权)人(译)	京东方科技集团股份有限公司.		
[标]发明人	HUANGFU LUJIANG FAN XING WANG DAN XU XIAOWEI LI LIANGJIAN		
发明人	HUANGFU, LUJIANG FAN, XING WANG, DAN XU, XIAOWEI LI, LIANGJIAN		
IPC分类号	H01L51/52 H01L27/32 H01L51/56		
CPC分类号	H01L27/3246 H01L51/5271 H01L51/56		
代理机构(译)	LAVOIX		
优先权	201710524515.5 2017-06-30 CN		
外部链接	Espacenet		

摘要(译)

提供了一种OLED显示基板，其制造方法和显示装置。OLED显示基板包括布置在基础基板上的TFT阵列层，第一电极，像素限定层，OEL层和第二电极。像素定义层被配置为定义多个子像素区域。反射结构围绕每个子像素区域，并且能够以使得至少一部分光束能够进入逃逸锥的方式来反射来自OEL层并超过逃逸锥的光束。

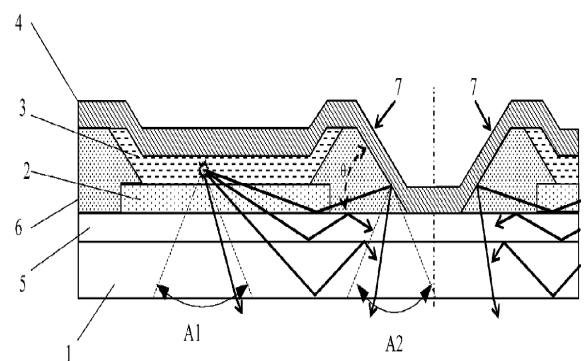


Fig.4